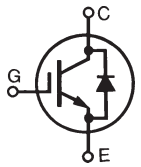
IXYS

Advance Technical Information

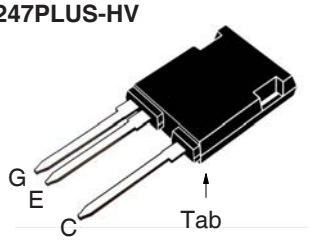
High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBX28N300HV

V_{CES} = 3000V
I_{C110} = 28A
$V_{CE(sat)}$ ≤ 2.7V



TO-247PLUS-HV



G = Gate E = Emitter
C = Collector Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	3000	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	3000	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	62	A
I_{C110}	T_C = 110°C	28	A
I_{CM}	T_C = 25°C, 1ms	200	A
SSOA	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 15Ω	I_{CM} = 220	A
(RBSOA)	Clamped Inductive Load	1500	V
T_{SC} **(SCSOA)**	V_{GE} = 15V, T_J = 125°C, R_G = 52Ω, V_{CE} = 1250V, Non-Repetitive	10	µs
P_C	T_C = 25°C	350	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	°C
F_C	Mounting Force	20..120/4.5..27	N/lb
Weight		6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250µA, V_{GE} = 0V	3000			V
$V_{GE(th)}$	I_C = 250µA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}, V_{GE} = 0V			25	µA
	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ± 25V			±200	nA
$V_{CE(sat)}$	I_C = 28A, V_{GE} = 15V, Note 1		2.3	2.7	V
	T_J = 125°C		2.8		V

Features

- High Blocking Voltage
- High Voltage Package
- Low Conduction Losses

Advantages

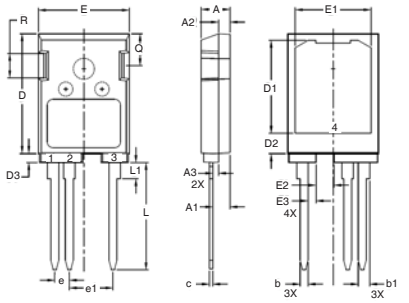
- Easy to Mount
- Space Savings
- High Power Density

Applications

- Uninterruptible Power Supplies (UPS)
- Switch-Mode and Resonant-Mode Power Supplies
- Capacitor Discharge Circuits
- Laser Generators

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 28A, V_{CE} = 10V, Note 1	14	24		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		2370		pF
C_{oes}			87		pF
C_{res}			30		pF
$Q_{g(on)}$	I_C = 28A, V_{GE} = 15V, V_{CE} = 1500V		110		nC
Q_{ge}			14		nC
Q_{gc}			50		nC
$t_{d(on)}$	**Resistive Switching Times, T_J = 25°C**		50		ns
t_r	I_C = 28A, V_{GE} = 15V		412		ns
$t_{d(off)}$	V_{CE} = 960V, R_G = 10Ω		125		ns
t_f			3660		ns
$t_{d(on)}$	**Resistive Switching Times, T_J = 125°C**		74		ns
t_r	I_C = 28A, V_{GE} = 15V		805		ns
$t_{d(off)}$	V_{CE} = 960V, R_G = 10Ω		245		ns
t_f			3280		ns
R_{thJC}				0.36	°C/W
R_{thCS}			0.15		°C/W

TO-247PLUS-HV Outline



1 - Gate
2,4 - Emitter
3 - Collector

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.193	.201	4.90	5.10
A1	.114	.122	2.90	3.10
A2	.075	.083	1.90	2.10
A3	.035	.043	0.90	1.10
b	.053	.059	1.35	1.50
b1	.075	.083	1.90	2.10
c	.022	.030	0.55	0.75
D	.819	.843	20.80	21.40
D1	.638	.646	16.20	16.40
D2	.134	.146	3.40	3.70
D3	.055	.063	1.40	1.60
E	.622	.638	15.80	16.20
E1	.520	.528	13.20	13.40
E2	.118	.126	3.00	3.20
E3	.051	.059	1.30	1.50
e	.100 BSC		2.54 BSC	
e1	.300 BSC		7.62 BSC	
L	.732	.748	18.60	19.00
L1	.106	.118	2.70	3.00
Q	.216	.224	5.50	5.70
R	.165	.169	4.20	4.30

Reverse Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
V_F	I_F = 28A, V_{GE} = 0V, Note 1			2.7	V
t_{rr}	I_F = 14A, V_{GE} = 0V, -di_F/dt = 100A/μs		1.5		μs
I_{RM}	V_R = 100V, V_{GE} = 0V		31.0		A
Q_{RM}			22.5		μC

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

Fig. 1. Output Characteristics @ T_J = 25ºC

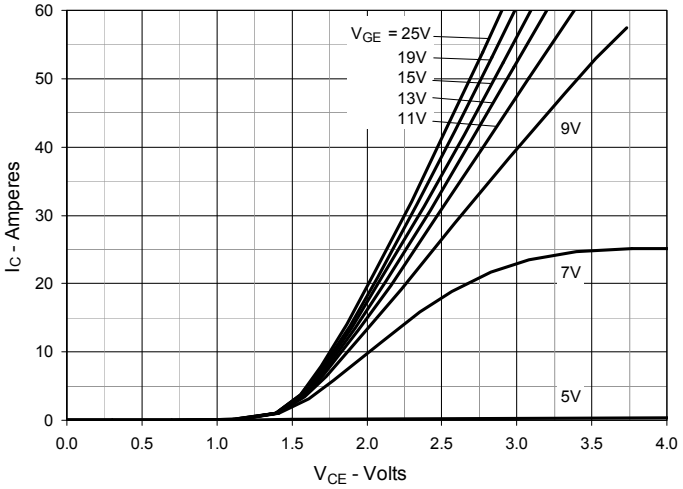


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

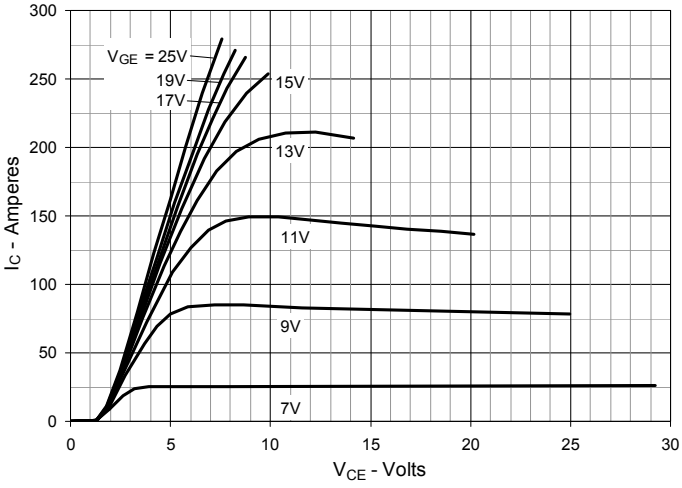


Fig. 3. Output Characteristics @ T_J = 125ºC

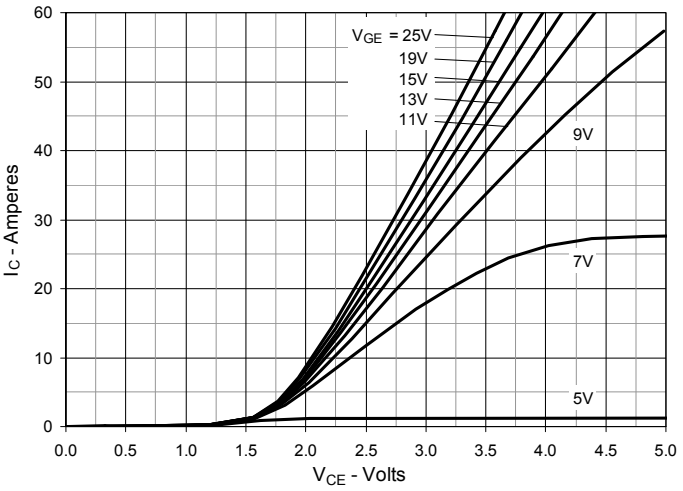


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

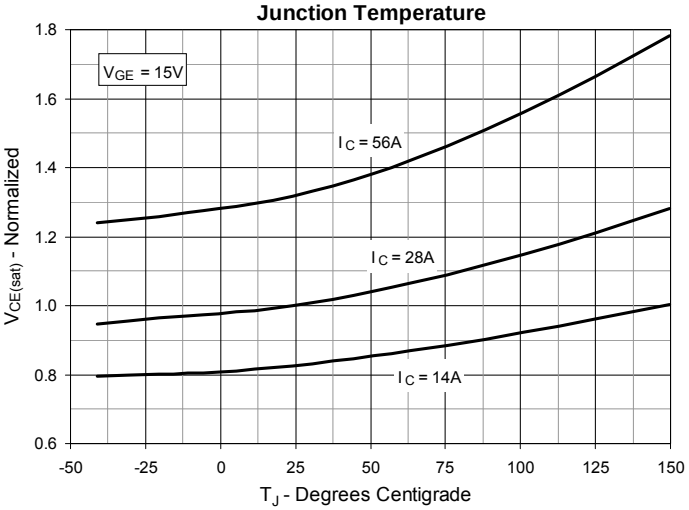


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

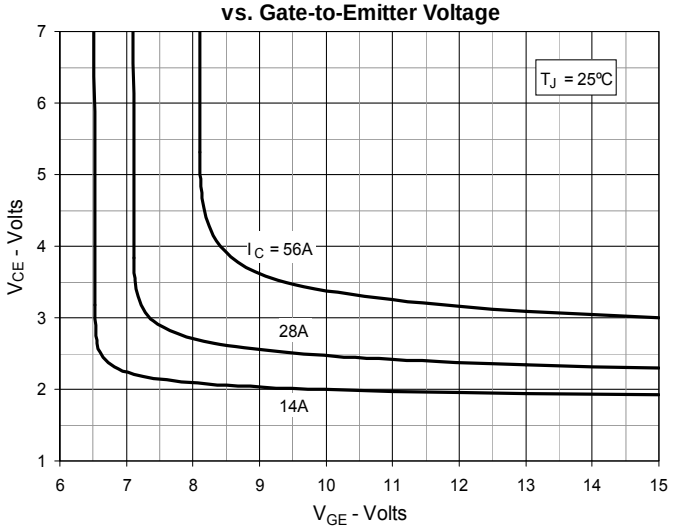


Fig. 6. Input Admittance

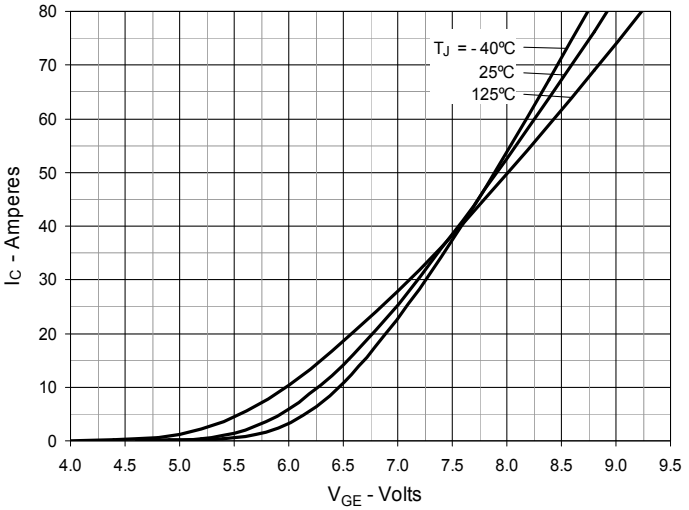


Fig. 7. Transconductance

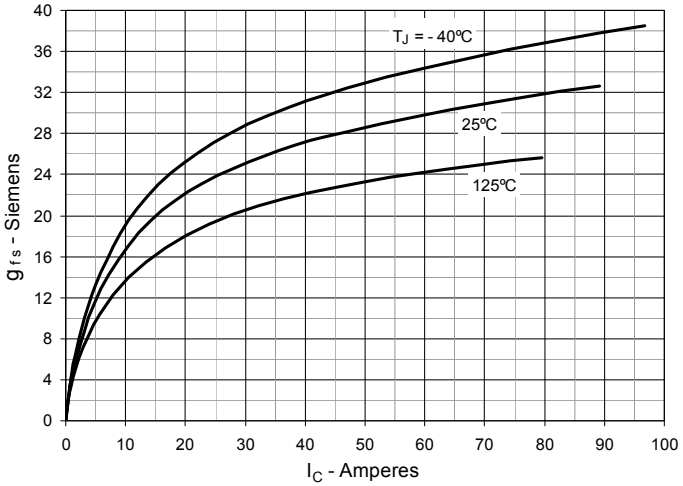


Fig. 8. Gate Charge

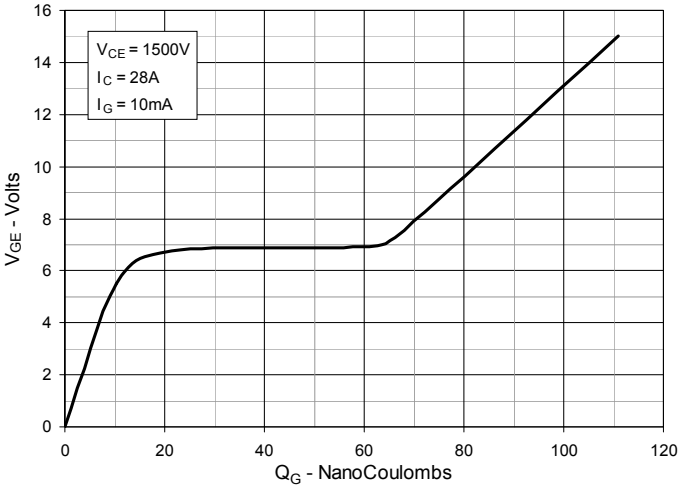


Fig. 9. Forward Voltage Drop of Intrinsic Diode

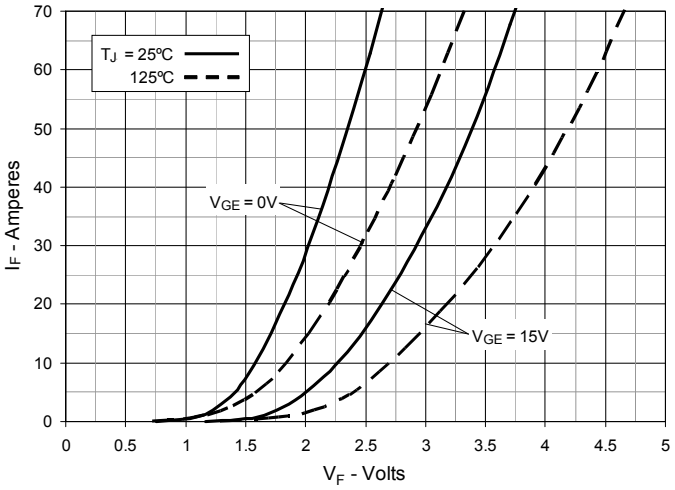


Fig. 10. Capacitance

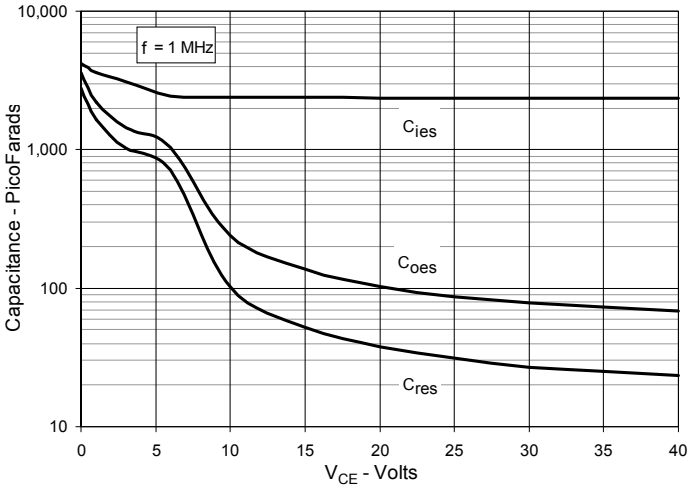


Fig. 11. Reverse-Bias Safe Operating Area

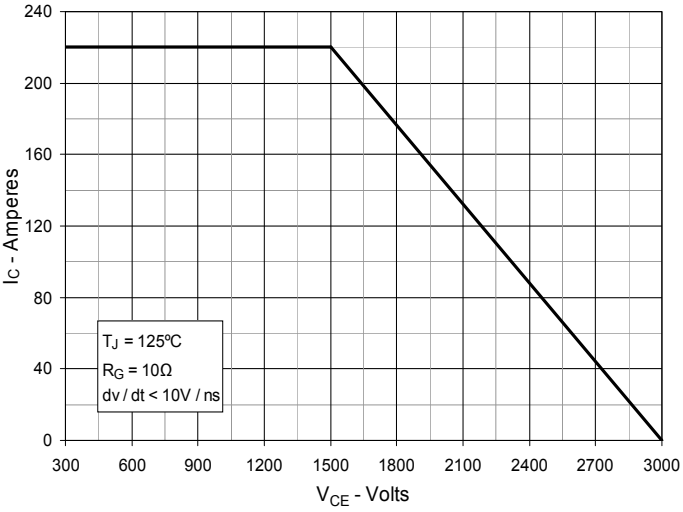


Fig. 12. Maximum Transient Thermal Impedance

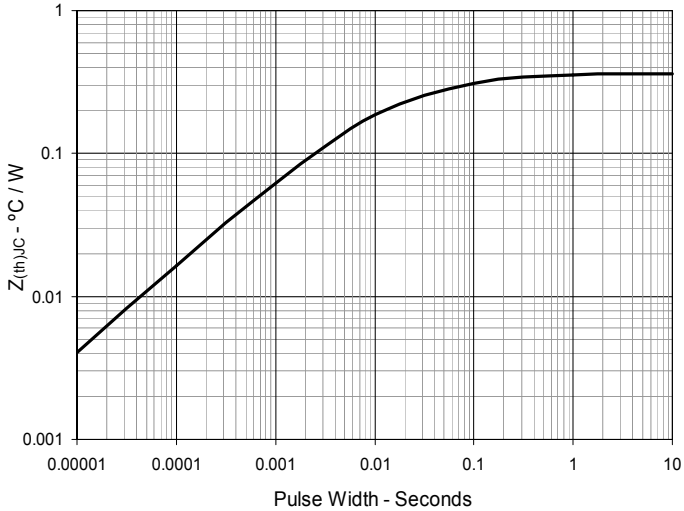


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 25ºC

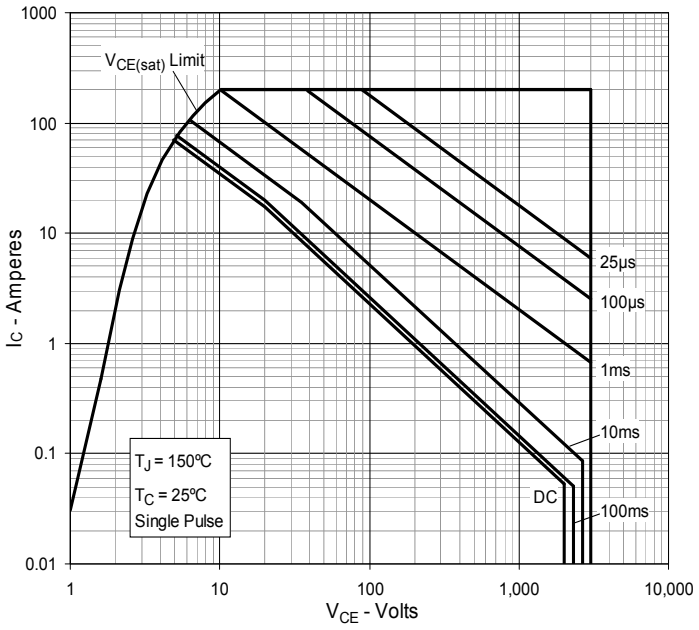


Fig. 14. Forward-Bias Safe Operating Area @ T_C = 75ºC